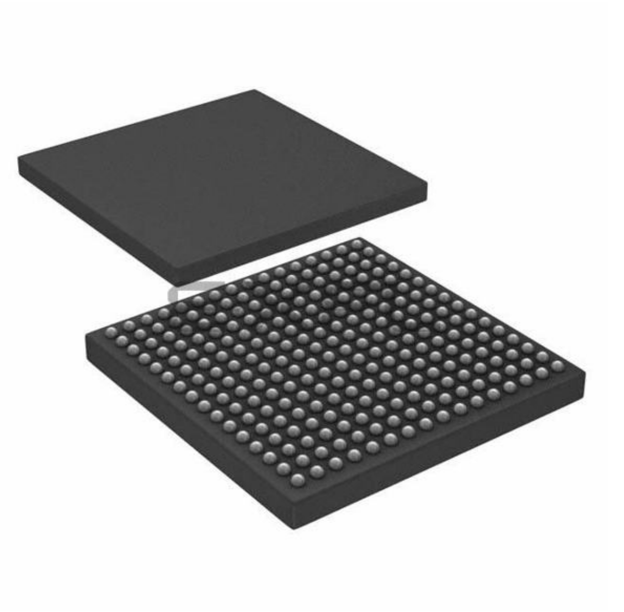
Microchip Technology - A3P600-2FGG256I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p600-2fgg256i

The absolute maximum junction temperature is 100°C. EQ 1 shows a sample calculation of the absolute maximum power dissipation allowed for a 484-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. } (°\text{C}) - \text{Max. ambient temp. } (°\text{C})}{\theta_{ja}(°\text{C/W})} = \frac{100°\text{C} - 70°\text{C}}{20.5°\text{C/W}} = 1.463\ \text{W}$$

EQ 1

Table 2-5 • **Package Thermal Resistivities**

Package Type	Device	Pin Count	θ_{jc}	θ_{ja}			Units
				Still Air	200 ft/min	500 ft/min	
Quad Flat No Lead	A3P030	132	0.4	21.4	16.8	15.3	°C/W
	A3P060	132	0.3	21.2	16.6	15.0	°C/W
	A3P125	132	0.2	21.1	16.5	14.9	°C/W
	A3P250	132	0.1	21.0	16.4	14.8	°C/W
Very Thin Quad Flat Pack (VQFP)	All devices	100	10.0	35.3	29.4	27.1	°C/W
Thin Quad Flat Pack (TQFP)	All devices	144	11.0	33.5	28.0	25.7	°C/W
Plastic Quad Flat Pack (PQFP)	All devices	208	8.0	26.1	22.5	20.8	°C/W
Fine Pitch Ball Grid Array (FBGA)	See note*	144	3.8	26.9	22.9	21.5	°C/W
	See note*	256	3.8	26.6	22.8	21.5	°C/W
	See note*	484	3.2	20.5	17.0	15.9	°C/W
	A3P1000	144	6.3	31.6	26.2	24.2	°C/W
	A3P1000	256	6.6	28.1	24.4	22.7	°C/W
	A3P1000	484	8.0	23.3	19.0	16.7	°C/W

Note: **This information applies to all ProASIC3 devices except the A3P1000. Detailed device/package thermal information will be available in future revisions of the datasheet.*

Temperature and Voltage Derating Factors

Table 2-6 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 70°C, VCC = 1.425 V)**

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.88	0.93	0.95	1.00	1.02	1.04
1.500	0.83	0.88	0.90	0.95	0.96	0.98
1.575	0.80	0.84	0.87	0.91	0.93	0.94

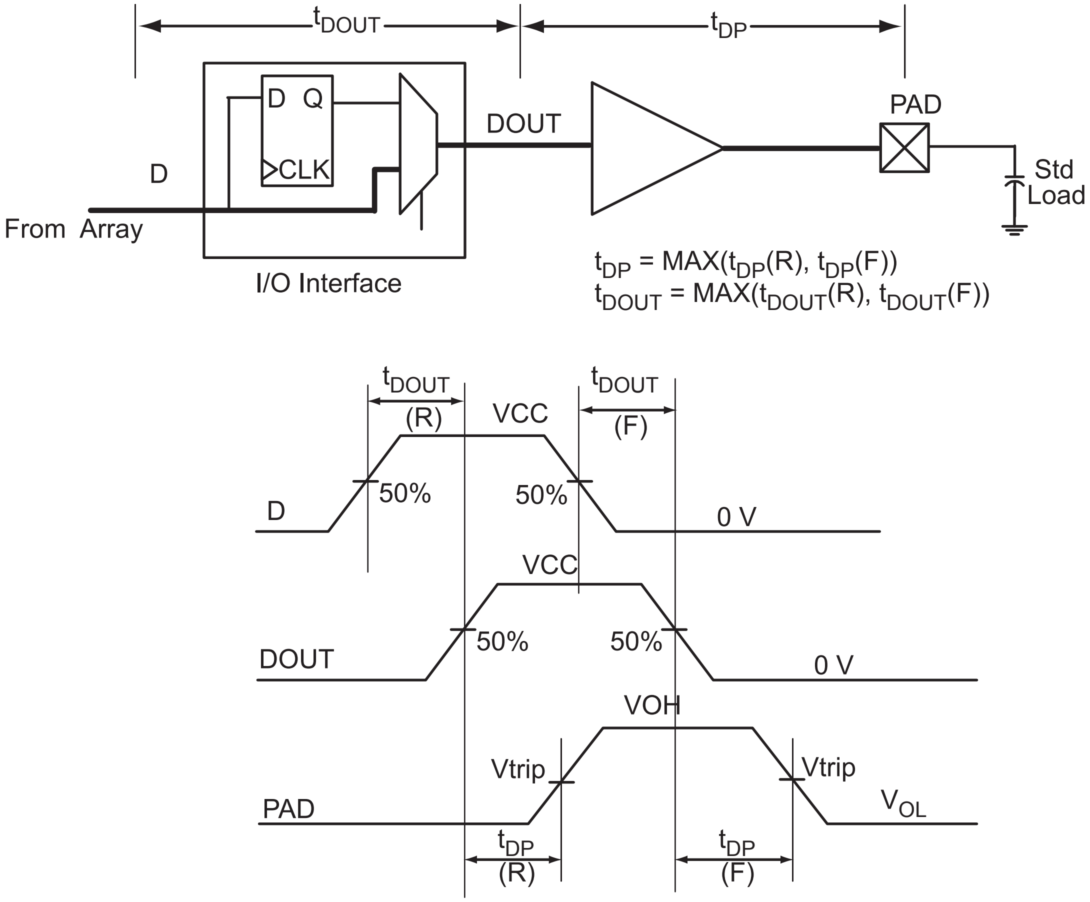

Figure 2-5 • **Output Buffer Model and Delays (Example)**

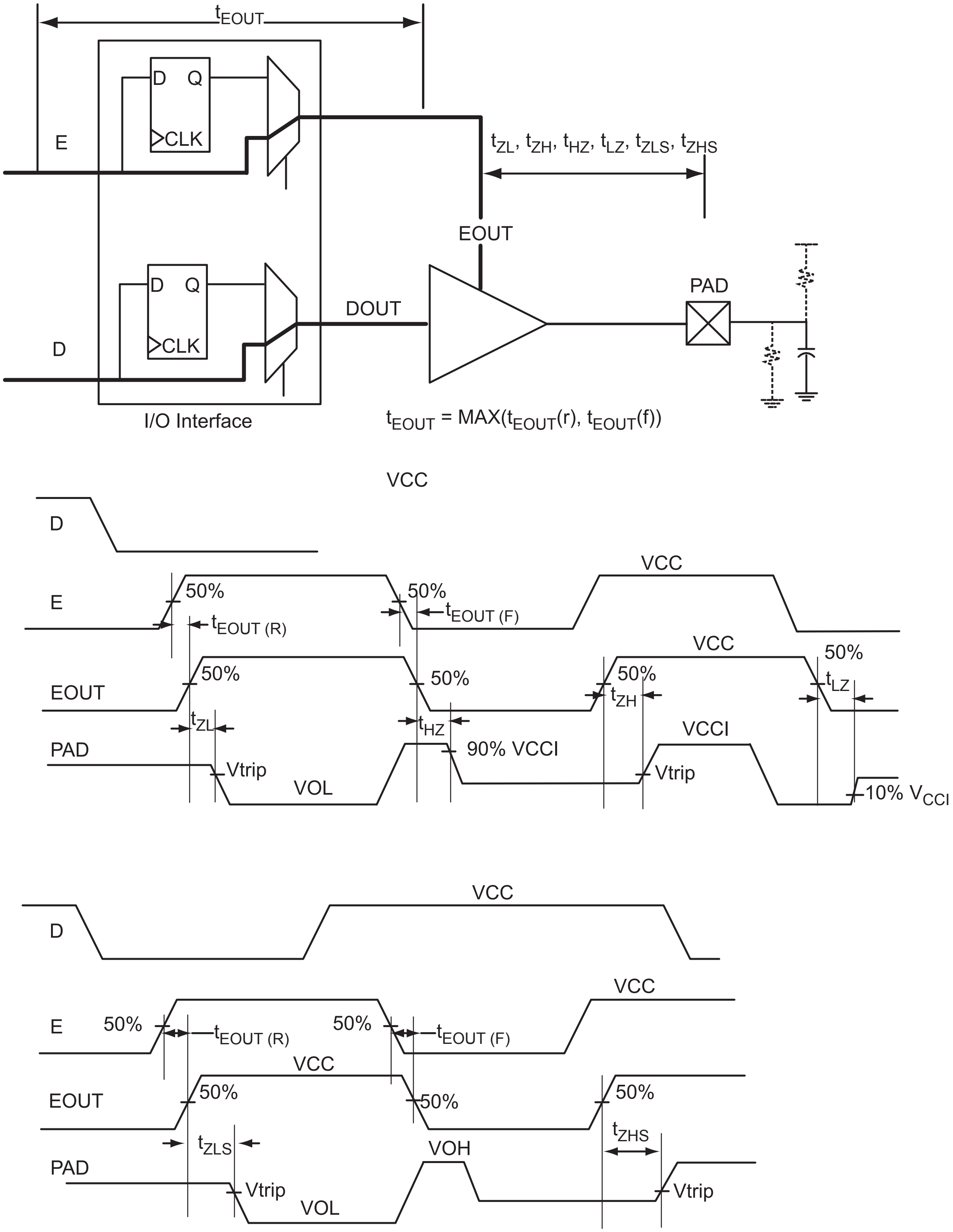

Figure 2-6 • **Tristate Output Buffer Timing Model and Delays (Example)**

I/O DC Characteristics

Table 2-27 • **Input Capacitance**

Symbol	Definition	Conditions	Min	Max	Units
C_{IN}	Input capacitance	VIN = 0, f = 1.0 MHz	–	8	pF
C_{INCLK}	Input capacitance on the clock pin	VIN = 0, f = 1.0 MHz	–	8	pF

Table 2-28 • **I/O Output Buffer Maximum Resistances[1]**
Applicable to Advanced I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
3.3 V LVCMOS Wide Range[4]	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at http://www.microsemi.com/soc/download/ibis/default.aspx.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)}$ *= (VOLspec) / IOLspec*
3. $R_{(PULL\text{-}UP\text{-}MAX)}$ *= (VCCImax – VOHspec) / IOHspec*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*

Timing Characteristics

Table 2-50 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.60	11.84	0.04	1.02	0.43	11.84	10.00	4.10	4.04	15.23	13.40	ns
		–1	0.51	10.07	0.04	0.86	0.36	10.07	8.51	3.48	3.44	12.96	11.40	ns
		–2	0.45	8.84	0.03	0.76	0.32	8.84	7.47	3.06	3.02	11.38	10.00	ns
100 µA	6 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 µA	8 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 µA	12 mA	Std.	0.60	5.46	0.04	1.02	0.43	5.46	4.29	4.97	5.54	8.86	7.68	ns
		–1	0.51	4.65	0.04	0.86	0.36	4.65	3.65	4.22	4.71	7.53	6.54	ns
		–2	0.45	4.08	0.03	0.76	0.32	4.08	3.20	3.71	4.14	6.61	5.74	ns
100 µA	16 mA	Std.	0.60	5.15	0.04	1.02	0.43	5.15	3.89	5.04	5.69	8.55	7.29	ns
		–1	0.51	4.38	0.04	0.86	0.36	4.38	3.31	4.29	4.84	7.27	6.20	ns
		–2	0.45	3.85	0.03	0.76	0.32	3.85	2.91	3.77	4.25	6.38	5.44	ns
100 µA	24 mA	Std.	0.60	4.75	0.04	1.02	0.43	4.75	3.22	5.14	6.28	8.15	6.61	ns
		–1	0.51	4.04	0.04	0.86	0.36	4.04	2.74	4.37	5.34	6.93	5.62	ns
		–2	0.45	3.55	0.03	0.76	0.32	3.55	2.40	3.84	4.69	6.09	4.94	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Software default selection highlighted in gray.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-62 • **2.5 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.28	0.04	1.30	0.43	7.41	8.28	2.25	2.07	9.64	10.51	ns
	–1	0.56	7.04	0.04	1.10	0.36	6.30	7.04	1.92	1.76	8.20	8.94	ns
	–2	0.49	6.18	0.03	0.97	0.32	5.53	6.18	1.68	1.55	7.20	7.85	ns
6 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
8 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
12 mA	Std.	0.66	3.21	0.04	1.30	0.43	3.27	3.14	2.82	3.11	5.50	5.38	ns
	–1	0.56	2.73	0.04	1.10	0.36	2.78	2.67	2.40	2.65	4.68	4.57	ns
	–2	0.49	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-63 • **2.5 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	10.84	0.04	1.30	0.43	10.64	10.84	2.26	1.99	12.87	13.08	ns
	–1	0.56	9.22	0.04	1.10	0.36	9.05	9.22	1.92	1.69	10.95	11.12	ns
	–2	0.49	8.10	0.03	0.97	0.32	7.94	8.10	1.68	1.49	9.61	9.77	ns
6 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
8 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
12 mA	Std.	0.66	5.63	0.04	1.30	0.43	5.73	5.51	2.83	3.01	7.97	7.74	ns
	–1	0.56	4.79	0.04	1.10	0.36	4.88	4.68	2.41	2.56	6.78	6.59	ns
	–2	0.49	4.20	0.03	0.97	0.32	4.28	4.11	2.11	2.25	5.95	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-66 • **Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks**

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA[3]	Max mA[3]	μA[4]	μA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	2	2	11	9	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	4	4	22	17	10	10
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	6	6	44	35	10	10
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	8	8	51	45	10	10
12 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	12	12	74	91	10	10
16 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	16	16	74	91	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-67 • **Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O I/O Banks**

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA[3]	Max mA[3]	μA[4]	μA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	11	9	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	22	17	10	10
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	6	6	44	35	10	10
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	8	8	44	35	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN <V CCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

***Table 2-72* • 1.8 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	11.33	0.04	1.20	0.43	8.72	11.33	2.24	1.52	10.96	13.57	ns
	–1	0.56	9.64	0.04	1.02	0.36	7.42	9.64	1.91	1.29	9.32	11.54	ns
	–2	0.49	8.46	0.03	0.90	0.32	6.51	8.46	1.68	1.14	8.18	10.13	ns
4 mA	Std.	0.66	6.48	0.04	1.20	0.43	5.48	6.48	2.65	2.60	7.72	8.72	ns
	–1	0.56	5.51	0.04	1.02	0.36	4.66	5.51	2.25	2.21	6.56	7.42	ns
	–2	0.49	4.84	0.03	0.90	0.32	4.09	4.84	1.98	1.94	5.76	6.51	ns
6 mA	Std.	0.66	4.06	0.04	1.20	0.43	3.84	4.06	2.93	3.10	6.07	6.30	ns
	–1	0.56	3.45	0.04	1.02	0.36	3.27	3.45	2.49	2.64	5.17	5.36	ns
	–2	0.49	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns
8 mA	Std.	0.66	4.06	0.04	1.20	0.43	3.84	4.06	2.93	3.10	6.07	6.30	ns
	–1	0.56	3.45	0.04	1.02	0.36	3.27	3.45	2.49	2.64	5.17	5.36	ns
	–2	0.49	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-73 • **1.8 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.80	0.04	1.20	0.43	13.49	14.80	2.25	1.46	15.73	17.04	ns
	–1	0.56	12.59	0.04	1.02	0.36	11.48	12.59	1.91	1.25	13.38	14.49	ns
	–2	0.49	11.05	0.03	0.90	0.32	10.08	11.05	1.68	1.09	11.75	12.72	ns
4 mA	Std.	0.66	9.90	0.04	1.20	0.43	9.73	9.90	2.65	2.50	11.97	12.13	ns
	–1	0.56	8.42	0.04	1.02	0.36	8.28	8.42	2.26	2.12	10.18	10.32	ns
	–2	0.49	7.39	0.03	0.90	0.32	7.27	7.39	1.98	1.86	8.94	9.06	ns
6 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns
8 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-74 • **1.8 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	–1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	–2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	–1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	–2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

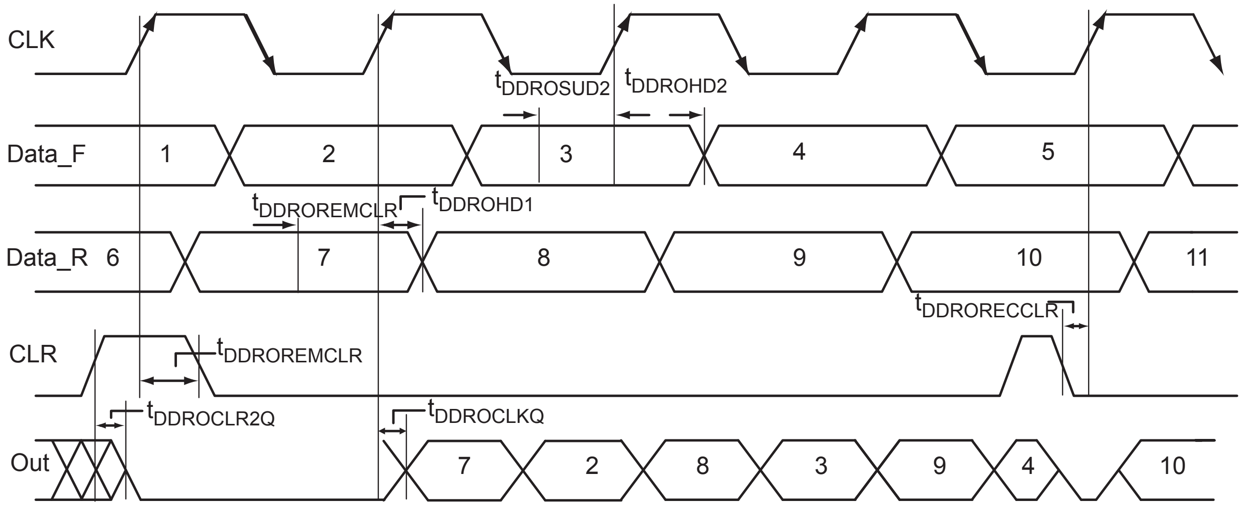

Figure 2-23 **• Output DDR Timing Diagram**

Timing Characteristics

Table 2-104 **• Output DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	0.70	0.80	0.94	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.38	0.43	0.51	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.38	0.43	0.51	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	0.80	0.91	1.07	ns
$t_{DDROREMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	0.00	ns
$t_{DDRORECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.22	0.25	0.30	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.22	0.25	0.30	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width High for the Output DDR	0.36	0.41	0.48	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width Low for the Output DDR	0.32	0.37	0.43	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	350	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Characteristics

***Table 2-105* • Combinatorial Cell Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Combinatorial Cell	Equation	Parameter	–2	–1	Std.	Units
INV	Y = !A	t_{PD}	0.40	0.46	0.54	ns
AND2	Y = A · B	t_{PD}	0.47	0.54	0.63	ns
NAND2	Y = !(A · B)	t_{PD}	0.47	0.54	0.63	ns
OR2	Y = A + B	t_{PD}	0.49	0.55	0.65	ns
NOR2	Y = !(A + B)	t_{PD}	0.49	0.55	0.65	ns
XOR2	$Y = A \oplus B$	t_{PD}	0.74	0.84	0.99	ns
MAJ3	Y = MAJ(A, B, C)	t_{PD}	0.70	0.79	0.93	ns
XOR3	$Y = A \oplus B \oplus C$	t_{PD}	0.87	1.00	1.17	ns
MUX2	Y = A !S + B S	t_{PD}	0.51	0.58	0.68	ns
AND3	Y = A · B · C	t_{PD}	0.56	0.64	0.75	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

VersaTile Specifications as a Sequential Module

The ProASIC3 library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the *Fusion, IGLOO/e, and ProASIC3/E Macro Library Guide*.

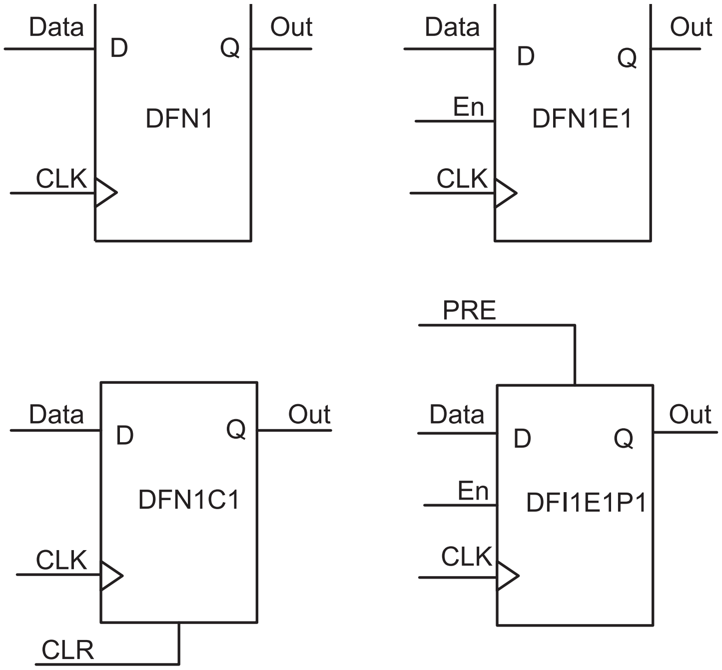

***Figure 2-26* • Sample of Sequential Cells**

FIFO

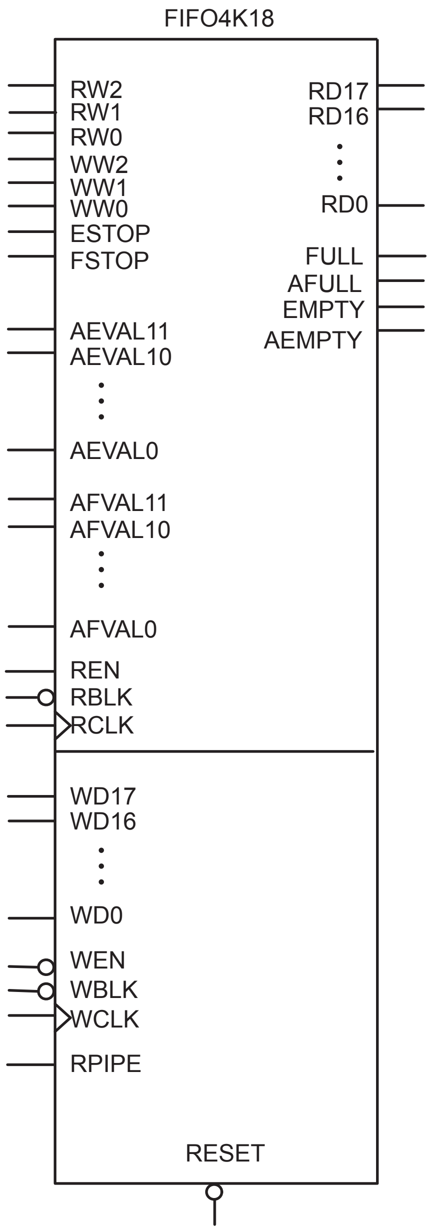

Figure 2-36 • **FIFO Model**

CS121	
Pin Number	**A3P060 Function**
K10	VPUMP
K11	GDB1/IO47RSB0
L1	VMV1
L2	GNDQ
L3	IO65RSB1
L4	IO63RSB1
L5	IO61RSB1
L6	IO58RSB1
L7	IO57RSB1
L8	IO55RSB1
L9	GNDQ
L10	GDA0/IO50RSB0
L11	VMV1

TQ144	
Pin Number	**A3P060 Function**
1	GAA2/IO51RSB1
2	IO52RSB1
3	GAB2/IO53RSB1
4	IO95RSB1
5	GAC2/IO94RSB1
6	IO93RSB1
7	IO92RSB1
8	IO91RSB1
9	VCC
10	GND
11	VCCIB1
12	IO90RSB1
13	GFC1/IO89RSB1
14	GFC0/IO88RSB1
15	GFB1/IO87RSB1
16	GFB0/IO86RSB1
17	VCOMPLF
18	GFA0/IO85RSB1
19	VCCPLF
20	GFA1/IO84RSB1
21	GFA2/IO83RSB1
22	GFB2/IO82RSB1
23	GFC2/IO81RSB1
24	IO80RSB1
25	IO79RSB1
26	IO78RSB1
27	GND
28	VCCIB1
29	GEC1/IO77RSB1
30	GEC0/IO76RSB1
31	GEB1/IO75RSB1
32	GEB0/IO74RSB1
33	GEA1/IO73RSB1
34	GEA0/IO72RSB1
35	VMV1
36	GNDQ
37	NC
38	GEA2/IO71RSB1
39	GEB2/IO70RSB1
40	GEC2/IO69RSB1
41	IO68RSB1
42	IO67RSB1
43	IO66RSB1
44	IO65RSB1
45	VCC
46	GND
47	VCCIB1
48	NC
49	IO64RSB1
50	NC
51	IO63RSB1
52	NC
53	IO62RSB1
54	NC
55	IO61RSB1
56	NC
57	NC
58	IO60RSB1
59	IO59RSB1
60	IO58RSB1
61	IO57RSB1
62	NC
63	GND
64	NC
65	GDC2/IO56RSB1
66	GDB2/IO55RSB1
67	GDA2/IO54RSB1
68	GNDQ
69	TCK
70	TDI
71	TMS
72	VMV1
73	VPUMP
74	NC
75	TDO
76	TRST
77	VJTAG
78	GDA0/IO50RSB0
79	GDB0/IO48RSB0
80	GDB1/IO47RSB0
81	VCCIB0
82	GND
83	IO44RSB0
84	GCC2/IO43RSB0
85	GCB2/IO42RSB0
86	GCA2/IO41RSB0
87	GCA0/IO40RSB0
88	GCA1/IO39RSB0
89	GCB0/IO38RSB0
90	GCB1/IO37RSB0
91	GCC0/IO36RSB0
92	GCC1/IO35RSB0
93	IO34RSB0
94	IO33RSB0
95	NC
96	NC
97	NC
98	VCCIB0
99	GND
100	VCC
101	IO30RSB0
102	GBC2/IO29RSB0
103	IO28RSB0
104	GBB2/IO27RSB0
105	IO26RSB0
106	GBA2/IO25RSB0
107	VMV0
108	GNDQ

PQ208	
Pin Number	**A3P250 Function**
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO115UDB3
9	IO115VDB3
10	IO114UDB3
11	IO114VDB3
12	IO113PDB3
13	IO113NDB3
14	IO112PDB3
15	IO112NDB3
16	VCC
17	GND
18	VCCIB3
19	IO111PDB3
20	IO111NDB3
21	GFC1/IO110PDB3
22	GFC0/IO110NDB3
23	GFB1/IO109PDB3
24	GFB0/IO109NDB3
25	VCOMPLF
26	GFA0/IO108NPB3
27	VCCPLF
28	GFA1/IO108PPB3
29	GND
30	GFA2/IO107PDB3
31	IO107NDB3
32	GFB2/IO106PDB3
33	IO106NDB3
34	GFC2/IO105PDB3
35	IO105NDB3
36	NC
37	IO104PDB3
38	IO104NDB3
39	IO103PSB3
40	VCCIB3
41	GND
42	IO101PDB3
43	IO101NDB3
44	GEC1/IO100PDB3
45	GEC0/IO100NDB3
46	GEB1/IO99PDB3
47	GEB0/IO99NDB3
48	GEA1/IO98PDB3
49	GEA0/IO98NDB3
50	VMV3
51	GNDQ
52	GND
53	NC
54	NC
55	GEA2/IO97RSB2
56	GEB2/IO96RSB2
57	GEC2/IO95RSB2
58	IO94RSB2
59	IO93RSB2
60	IO92RSB2
61	IO91RSB2
62	VCCIB2
63	IO90RSB2
64	IO89RSB2
65	GND
66	IO88RSB2
67	IO87RSB2
68	IO86RSB2
69	IO85RSB2
70	IO84RSB2
71	VCC
72	VCCIB2
73	IO83RSB2
74	IO82RSB2
75	IO81RSB2
76	IO80RSB2
77	IO79RSB2
78	IO78RSB2
79	IO77RSB2
80	IO76RSB2
81	GND
82	IO75RSB2
83	IO74RSB2
84	IO73RSB2
85	IO72RSB2
86	IO71RSB2
87	IO70RSB2
88	VCC
89	VCCIB2
90	IO69RSB2
91	IO68RSB2
92	IO67RSB2
93	IO66RSB2
94	IO65RSB2
95	IO64RSB2
96	GDC2/IO63RSB2
97	GND
98	GDB2/IO62RSB2
99	GDA2/IO61RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

PQ208	
Pin Number	**A3P400 Function**
1	GND
2	GAA2/IO155UDB3
3	IO155VDB3
4	GAB2/IO154UDB3
5	IO154VDB3
6	GAC2/IO153UDB3
7	IO153VDB3
8	IO152UDB3
9	IO152VDB3
10	IO151UDB3
11	IO151VDB3
12	IO150PDB3
13	IO150NDB3
14	IO149PDB3
15	IO149NDB3
16	VCC
17	GND
18	VCCIB3
19	IO148PDB3
20	IO148NDB3
21	GFC1/IO147PDB3
22	GFC0/IO147NDB3
23	GFB1/IO146PDB3
24	GFB0/IO146NDB3
25	VCOMPLF
26	GFA0/IO145NPB3
27	VCCPLF
28	GFA1/IO145PPB3
29	GND
30	GFA2/IO144PDB3
31	IO144NDB3
32	GFB2/IO143PDB3
33	IO143NDB3
34	GFC2/IO142PDB3
35	IO142NDB3
36	NC

PQ208	
Pin Number	**A3P400 Function**
37	IO141PSB3
38	IO140PDB3
39	IO140NDB3
40	VCCIB3
41	GND
42	IO138PDB3
43	IO138NDB3
44	GEC1/IO137PDB3
45	GEC0/IO137NDB3
46	GEB1/IO136PDB3
47	GEB0/IO136NDB3
48	GEA1/IO135PDB3
49	GEA0/IO135NDB3
50	VMV3
51	GNDQ
52	GND
53	VMV2
54	NC
55	GEA2/IO134RSB2
56	GEB2/IO133RSB2
57	GEC2/IO132RSB2
58	IO131RSB2
59	IO130RSB2
60	IO129RSB2
61	IO128RSB2
62	VCCIB2
63	IO125RSB2
64	IO123RSB2
65	GND
66	IO121RSB2
67	IO119RSB2
68	IO117RSB2
69	IO115RSB2
70	IO113RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	**A3P400 Function**
73	IO112RSB2
74	IO111RSB2
75	IO110RSB2
76	IO109RSB2
77	IO108RSB2
78	IO107RSB2
79	IO106RSB2
80	IO104RSB2
81	GND
82	IO102RSB2
83	IO101RSB2
84	IO100RSB2
85	IO99RSB2
86	IO98RSB2
87	IO97RSB2
88	VCC
89	VCCIB2
90	IO94RSB2
91	IO92RSB2
92	IO90RSB2
93	IO88RSB2
94	IO86RSB2
95	IO84RSB2
96	GDC2/IO82RSB2
97	GND
98	GDB2/IO81RSB2
99	GDA2/IO80RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

FG256	
Pin Number	**A3P400 Function**
P9	IO98RSB2
P10	IO95RSB2
P11	IO88RSB2
P12	IO84RSB2
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO79VDB1
R1	GEA1/IO135PDB3
R2	GEA0/IO135NDB3
R3	IO127RSB2
R4	GEC2/IO132RSB2
R5	IO123RSB2
R6	IO118RSB2
R7	IO112RSB2
R8	IO106RSB2
R9	IO100RSB2
R10	IO96RSB2
R11	IO89RSB2
R12	IO85RSB2
R13	GDB2/IO81RSB2
R14	TDI
R15	NC
R16	TDO
T1	GND
T2	IO126RSB2
T3	GEB2/IO133RSB2
T4	IO124RSB2
T5	IO116RSB2
T6	IO113RSB2
T7	IO107RSB2
T8	IO105RSB2
T9	IO102RSB2
T10	IO97RSB2
T11	IO92RSB2
T12	GDC2/IO82RSB2
T13	IO86RSB2
T14	GDA2/IO80RSB2
T15	TMS
T16	GND

FG256	
Pin Number	**A3P1000 Function**
H3	GFB1/IO208PPB3
H4	VCOMPLF
H5	GFC0/IO209NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO91NPB1
H13	GCB1/IO92PPB1
H14	GCA0/IO93NPB1
H15	IO96NPB1
H16	GCB0/IO92NPB1
J1	GFA2/IO206PSB3
J2	GFA1/IO207PDB3
J3	VCCPLF
J4	IO205NDB3
J5	GFB2/IO205PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO95PPB1
J13	GCA1/IO93PPB1
J14	GCC2/IO96PPB1
J15	IO100PPB1
J16	GCA2/IO94PSB1
K1	GFC2/IO204PDB3
K2	IO204NDB3
K3	IO203NDB3
K4	IO203PDB3
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO95NPB1
K14	IO100NPB1
K15	IO102NDB1
K16	IO102PDB1
L1	IO202NDB3
L2	IO202PDB3
L3	IO196PPB3
L4	IO193PPB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO112NPB1
L14	IO106NDB1
L15	IO106PDB1
L16	IO107PDB1
M1	IO197NSB3
M2	IO196NPB3
M3	IO193NPB3
M4	GEC0/IO190NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO147RSB2
M9	IO136RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO110NDB1
M14	GDB1/IO112PPB1
M15	GDC1/IO111PDB1
M16	IO107NDB1
N1	IO194PSB3
N2	IO192PPB3
N3	GEC1/IO190PPB3
N4	IO192NPB3
N5	GNDQ
N6	GEA2/IO187RSB2
N7	IO161RSB2
N8	IO155RSB2
N9	IO141RSB2
N10	IO129RSB2
N11	IO124RSB2
N12	GNDQ
N13	IO110PDB1
N14	VJTAG
N15	GDC0/IO111NDB1
N16	GDA1/IO113PDB1
P1	GEB1/IO189PDB3
P2	GEB0/IO189NDB3
P3	VMV2
P4	IO179RSB2
P5	IO171RSB2
P6	IO165RSB2
P7	IO159RSB2
P8	IO151RSB2
P9	IO137RSB2
P10	IO134RSB2
P11	IO128RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO113NDB1
R1	GEA1/IO188PDB3
R2	GEA0/IO188NDB3
R3	IO184RSB2
R4	GEC2/IO185RSB2

Revision	Changes	Page
Revision 5 (Aug 2008) DC and Switching Characteristics v1.3	TJ, Maximum Junction Temperature, was changed to 100° from 110º in the "Thermal Characteristics" section and EQ 1. The calculated result of Maximum Power Allowed has thus changed to 1.463 W from 1.951 W.	2-6
	Values for the A3P015 device were added to Table 2-7 • Quiescent Supply Current Characteristics.	2-7
	Values for the A3P015 device were added to Table 2-14 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices. P_{AC14} was removed. Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices is new.	2-11, 2-12
	The "PLL Contribution—PPLL" section was updated to change the P_{PLL} formula from $P_{AC13} + P_{AC14} * F_{CLKOUT}$ to $P_{DC4} + P_{AC13} * F_{CLKOUT}$.	2-14
	Both fall and rise values were included for $t_{DDRISUD}$ and t_{DDRIHD} in Table 2-102 • Input DDR Propagation Delays.	2-78
	Table 2-107 • A3P015 Global Resource is new.	2-86
	The typical value for Delay Increments in Programmable Delay Blocks was changed from 160 to 200 in Table 2-115 • ProASIC3 CCC/PLL Specification.	2-90
Revision 4 (Jun 2008) DC and Switching Characteristics v1.2	Table note references were added to Table 2-2 • Recommended Operating Conditions 1, and the order of the table notes was changed.	2-2
	The title for Table 2-4 • Overshoot and Undershoot Limits 1 was modified to remove "as measured on quiet I/Os." Table note 1 was revised to remove "estimated SSO density over cycles." Table note 2 was revised to remove "refers only to overshoot/undershoot limits for simultaneous switching I/Os."	2-3
	The "Power per I/O Pin" section was updated to include 3 additional tables pertaining to input buffer power and output buffer power.	2-7
	Table 2-29 • I/O Output Buffer Maximum Resistances 1 was revised to include values for 3.3 V PCI/PCI-X.	2-27
	Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels was updated.	2-66
Revision 3 (Jun 2008) Packaging v1.3	Pin numbers were added to the "QN68 – Bottom View" package diagram. Note 2 was added below the diagram.	4-3
	The "QN132 – Bottom View" package diagram was updated to include D1 to D4. In addition, note 1 was changed from top view to bottom view, and note 2 is new.	4-6
Revision 2 (Feb 2008) Product Brief v1.0	This document was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
	This document was updated to include A3P015 device information. QN68 is a new package that was added because it is offered in the A3P015. The following sections were updated: "Features and Benefits" "ProASIC3 Ordering Information" "Temperature Grade Offerings" "ProASIC3 Flash Family FPGAs" "A3P015 and A3P030" note Introduction and Overview (NA)	N/A

Revision	Changes	Page
v2.0 (continued)	Table 3-20 • Summary of I/O Timing Characteristics—Software Default Settings (Advanced) and Table 3-21 • Summary of I/O Timing Characteristics—Software Default Settings (Standard Plus) were updated.	3-20 to 3-20
	Table 3-11 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices was updated.	3-9
	Table 3-24 • I/O Output Buffer Maximum Resistances1 (Advanced) and Table 3-25 • I/O Output Buffer Maximum Resistances1 (Standard Plus) were updated.	3-22 to 3-22
	Table 3-17 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions was updated.	3-18
	Table 3-28 • I/O Short Currents IOSH/IOSL (Advanced) and Table 3-29 • I/O Short Currents IOSH/IOSL (Standard Plus) were updated.	3-24 to 3-26
	The note in Table 3-32 • I/O Input Rise Time, Fall Time, and Related I/O Reliability was updated.	3-27
	Figure 3-33 • Write Access After Write onto Same Address, Figure 3-34 • Read Access After Write onto Same Address, and Figure 3-35 • Write Access After Read onto Same Address are new.	3-82 to 3-84
	Figure 3-43 • Timing Diagram was updated.	3-96
	Ambient was deleted from the "Speed Grade and Temperature Grade Matrix".	iv
	Notes were added to the package diagrams identifying if they were top or bottom view.	N/A
	The A3P030 "132-Pin QFN" table is new.	4-2
	The A3P060 "132-Pin QFN" table is new.	4-4
	The A3P125 "132-Pin QFN" table is new.	4-6
	The A3P250 "132-Pin QFN" table is new.	4-8
	The A3P030 "100-Pin VQFP" table is new.	4-11
Advance v0.7 (January 2007)	In the "I/Os Per Package" table, the I/O numbers were added for A3P060, A3P125, and A3P250. The A3P030-VQ100 I/O was changed from 79 to 77.	ii
Advance v0.6 (April 2006)	The term flow-through was changed to pass-through.	N/A
	Table 1 was updated to include the QN132.	ii
	The "I/Os Per Package" table was updated with the QN132. The footnotes were also updated. The A3P400-FG144 I/O count was updated.	ii
	"Automotive ProASIC3 Ordering Information" was updated with the QN132.	iii
	"Temperature Grade Offerings" was updated with the QN132.	iii
	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-7 • Efficient Long-Line Resources was updated.	2-7
	The footnotes in Figure 2-15 • Clock Input Sources Including CLKBUF, CLKBUF_LVDS/LVPECL, and CLKINT were updated.	2-16
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21